

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

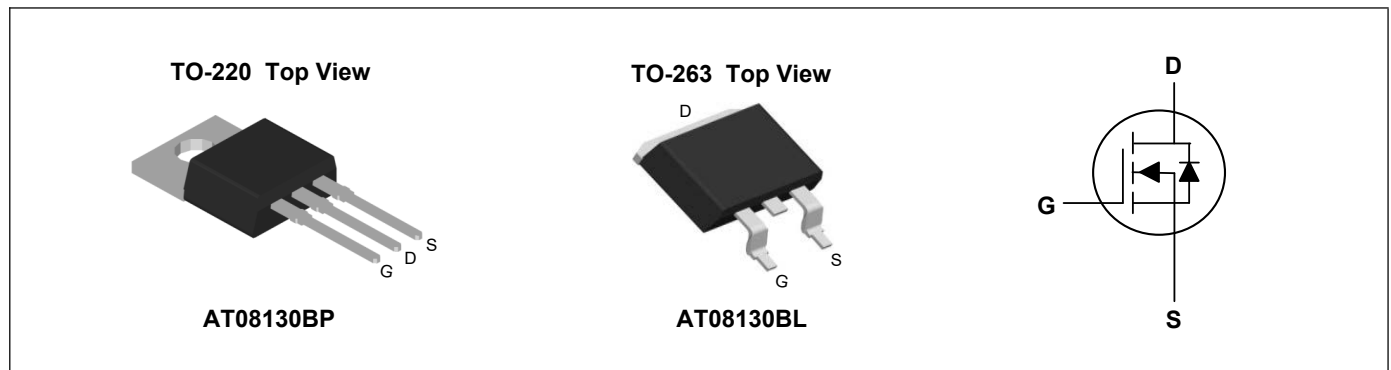
Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- UPS Inverter

Product Summary



V_{DS}	85	V
I_D	130	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4.8	m Ω



Absolute Maximum Ratings($T_C=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_{D@T_C=25^\circ C}$	130	A
Continuous Drain Current ¹	$I_{D@T_C=100^\circ C}$	92	A
Pulsed Drain Current ²	I_{DM}	400	A
Single Pulse Avalanche Energy ³	E_{AS}	211	mJ
Avalanche Current	I_{AS}	65	A
Total Power Dissipation ⁴	$P_D@T_C=25^\circ C$	154	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	60	$^\circ C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	0.81	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	85	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =30A	---	4	4.8	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	2	3	4	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =3A	---	13	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.3	---	Ω
Total Gate Charge	Q _g	V _{DD} =40V, V _{GS} =10V, I _D =50A	---	32	---	nC
Gate-Source Charge	Q _{gs}		---	9.5	---	
Gate-Drain Charge	Q _{gd}		---	10	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =40V, V _{GS} =10V, R _G =6Ω, I _D =50A	---	10	---	ns
Rise Time	T _r		---	15	---	
Turn-Off Delay Time	T _{d(off)}		---	30	---	
Fall Time	T _f		---	35	---	
Input Capacitance	C _{iss}	V _{DS} =40V, V _{GS} =0V, f=1MHz	---	2400	---	pF
Output Capacitance	C _{oss}		---	540	---	
Reverse Transfer Capacitance	C _{rss}		---	15	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	0.8	1.2	V
Reverse Recovery Time	t _{rr}	I _S =10A, V _R =50V di/dt=100A/μs, T _J =25°C	---	50	---	nS
Reverse Recovery Charge	Q _{rr}		---	80	---	nC

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD}=50V, V_{GS}=10V, L=0.1mH
4. The power dissipation is limited by 150°C junction temperature

Typical Characteristics

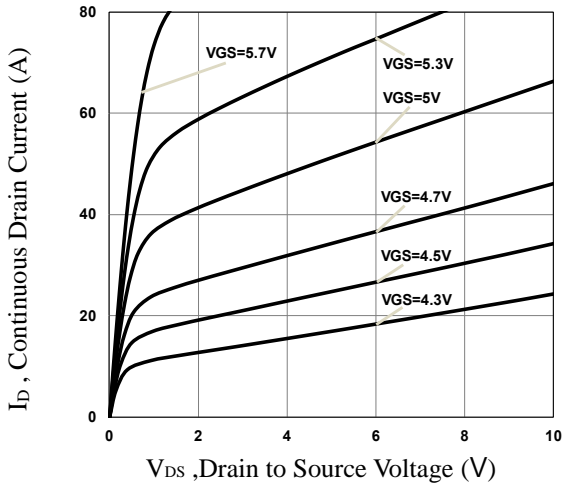


Fig.1 Typical Output Characteristics

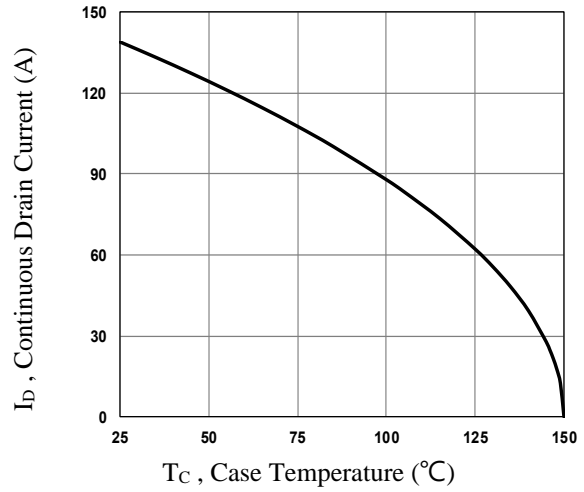


Fig.2 Continuous Drain Current vs. T_C

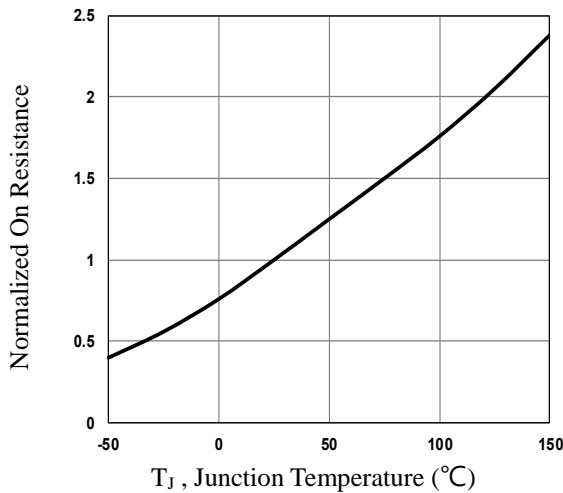


Fig.3 Normalized $R_{DS(on)}$ vs. T_J

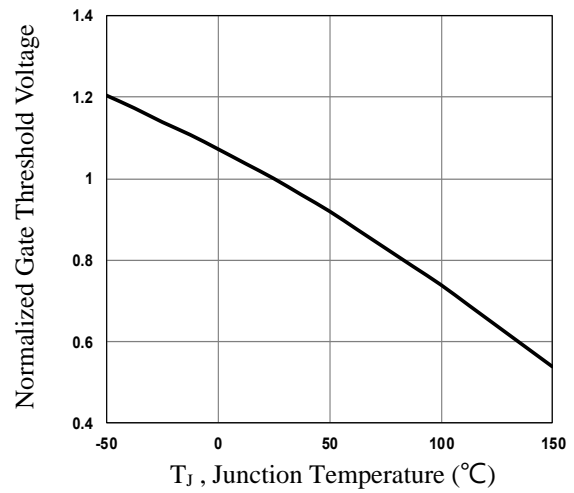


Fig.4 Normalized V_{th} vs. T_J

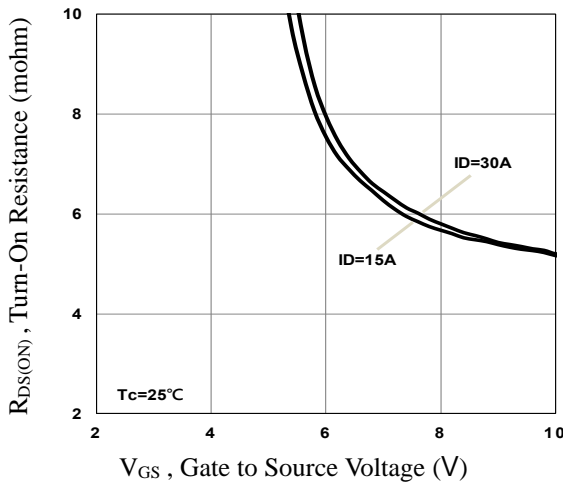


Fig.5 Turn-On Resistance vs. V_{GS}

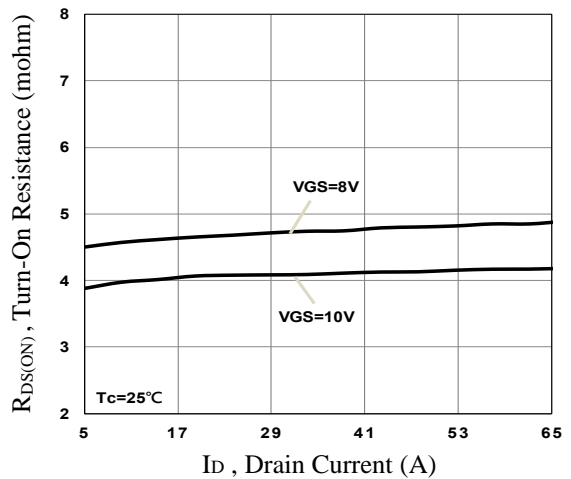


Fig.6 Turn-On Resistance vs. I_D

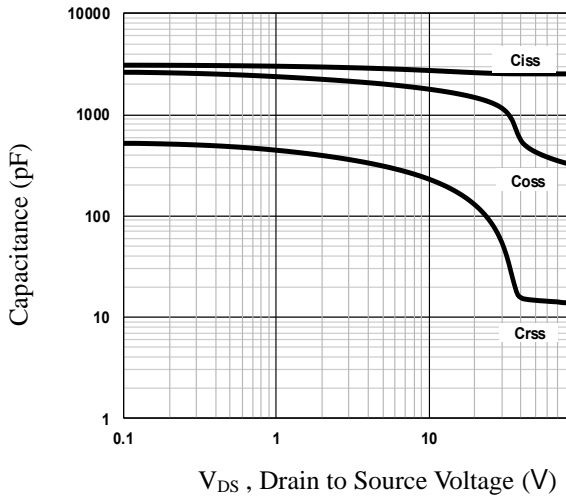


Fig.7 Capacitance Characteristics

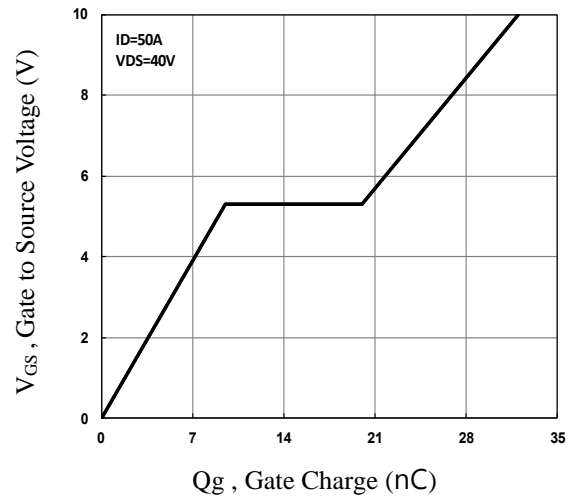


Fig.8 Gate Charge Characteristics

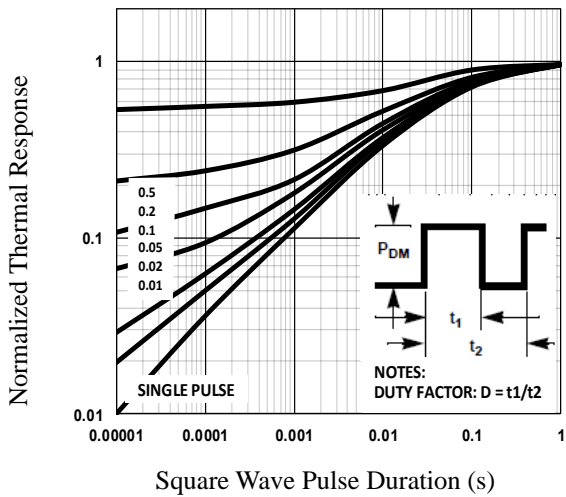


Fig.9 Normalized Transient Impedance

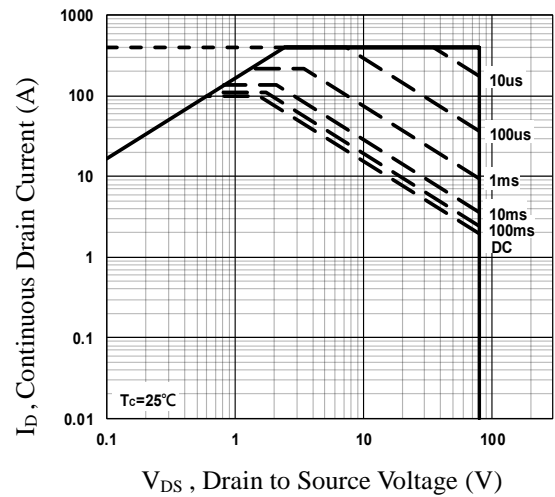
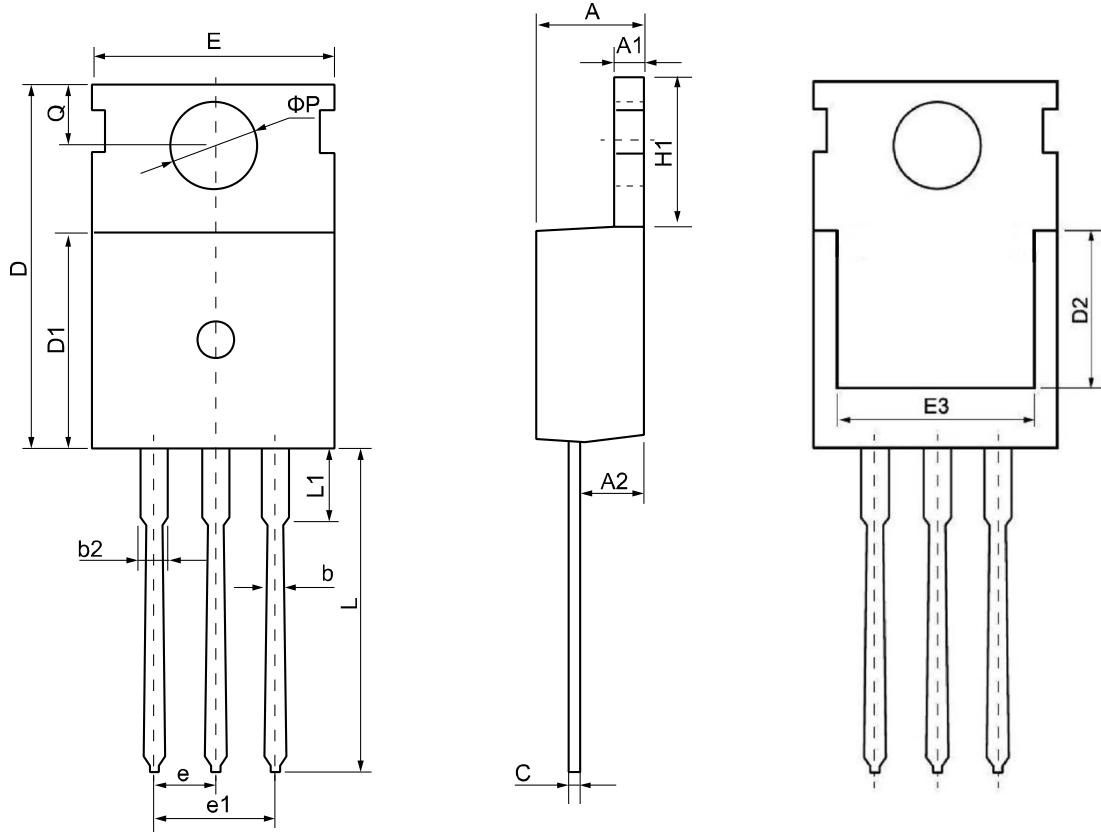


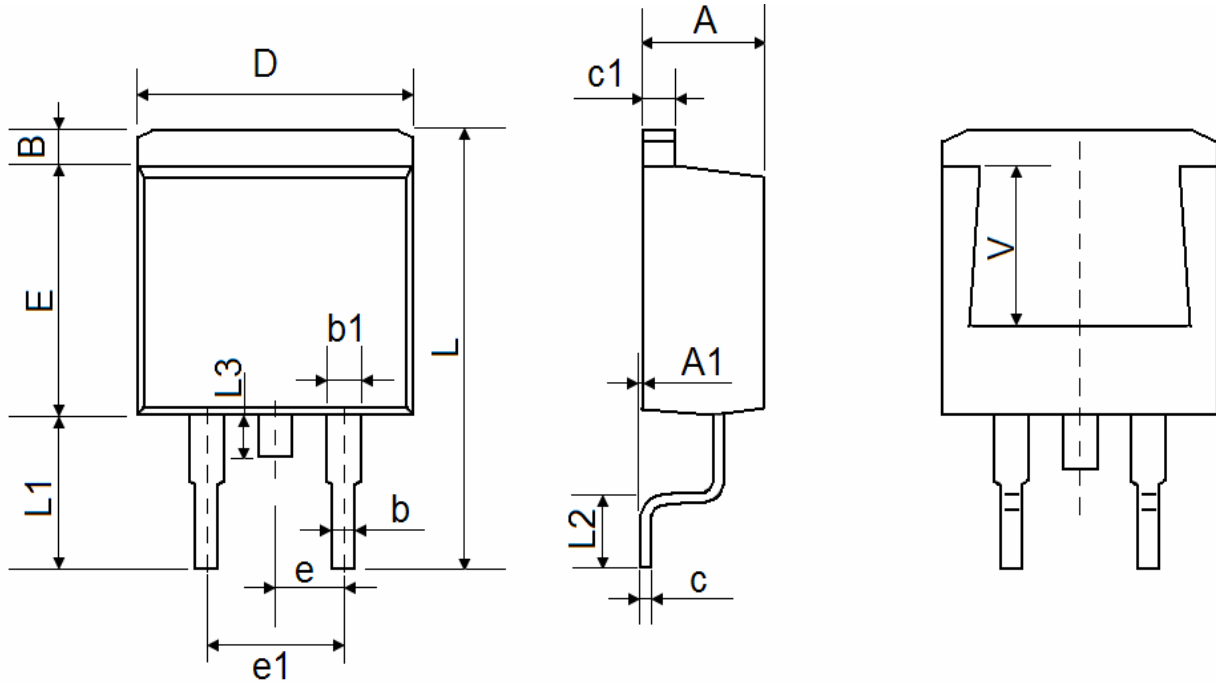
Fig.10 Maximum Safe Operation Area

TO-220 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.30	4.55	4.75	E	9.65	10.00	10.25
A1	1.15	1.30	1.45	E3	7.00	--	--
A2	2.20	2.40	2.60	e	2.54 BSC		
b	0.70	0.80	0.95	e1	5.08 BSC		
b2	1.17	1.27	1.47	H1	6.30	6.50	6.80
c	0.40	0.50	0.65	L	12.70	13.50	14.10
D	15.30	15.60	15.90	L1	--	3.20	3.95
D1	8.90	9.10	9.35	ϕP	3.40	3.60	3.80
D2	5.50	--	--	Q	2.60	2.80	3.00

TO-263 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.40	4.55	4.70	A1	0.00	0.07	0.15
B	1.00	1.20	1.40	b	0.65	0.80	0.95
b1	1.10	1.15	1.37	c	0.30	0.40	0.53
c1	1.10	1.25	1.37	D	9.80	10.00	10.40
E	8.50	8.80	9.20	e	2.54 REF		
e1	4.90	5.10	5.40	L	14.80	15.20	15.70
L1	5.00	5.25	5.60	L2	2.05	2.45	2.80
L3	1.20	1.50	1.80	V	5.60 REF		